

# 2N3821

# 2N3822

# 2N3824

**CASE 20-03, STYLE 1  
TO-72 (TO-206AF)**

**JFET  
LOW FREQUENCY, LOW NOISE**

**N-CHANNEL — DEPLETION  
JAN 2N3821 AND JAN 2N3822 AVAILABLE**

Refer to 2N4220 for graphs.

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	50	Vdc
Drain-Gate Voltage	V <sub>DG</sub>	50	Vdc
Gate-Source Voltage	V <sub>GS</sub>	-50	Vdc
Drain Current	I <sub>D</sub>	10	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.0	mW mW/°C
Junction Temperature Range	T <sub>J</sub>	175	°C
Storage Temperature Range	T <sub>Stg</sub>	-65 to +200	°C

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**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)**

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Gate-Source Breakdown Voltage (I <sub>G</sub> = -1.0 μAdc, V <sub>DS</sub> = 0)	V <sub>(BR)GSS</sub>	-50	—	Vdc
Gate Reverse Current (V <sub>GS</sub> = -30 Vdc, V <sub>DS</sub> = 0) (V <sub>GS</sub> = -30 Vdc, V <sub>DS</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>GSS</sub>	—	-0.1 -100	nAdc
Gate Source Cutoff Voltage (I <sub>D</sub> = 0.5 nAdc, V <sub>DS</sub> = 15 Vdc)	V <sub>GS(off)</sub>	—	-4.0 -6.0	Vdc
Gate Source Voltage (I <sub>D</sub> = 50 μAdc, V <sub>DS</sub> = 15 Vdc) (I <sub>D</sub> = 200 μAdc, V <sub>DS</sub> = 15 Vdc)	V <sub>GS</sub>	-0.5 -1.0	-2.0 -4.0	Vdc
Drain Cutoff Current (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = -8.0 Vdc) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = -8.0 Vdc, T <sub>A</sub> = 150°C)	I <sub>D(off)</sub>	—	0.1 100	nAdc

## ON CHARACTERISTICS

Zero-Gate-Voltage Drain Current(1) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0)	I <sub>DSS</sub>	0.5 2.0	2.5 10	mAdc
Static Drain-Source On Resistance (V <sub>GS</sub> = 0, I <sub>D</sub> = 0, f = 1.0 kHz)	r <sub>DS(on)</sub>	—	250	Ohms

## SMALL-SIGNAL CHARACTERISTICS

Forward Transfer Admittance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 kHz)(1)	Y <sub>fs</sub>	1500 3000	4500 6500	μmhos
(V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 100 MHz)	—	1500 3000	—	—
Output Admittance(1) (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 kHz)	Y <sub>os</sub>	—	10 20	μmhos
Input Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>iss</sub>	—	6.0	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 15 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>rss</sub>	—	3.0 3.0	pF
(V <sub>GS</sub> = -8.0 Vdc, V <sub>DS</sub> = 0, f = 1.0 MHz)	—	—	3.0	—

**2N3821, 2N3822, 2N3824****ELECTRICAL CHARACTERISTICS** (continued) ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
<b>FUNCTIONAL CHARACTERISTICS</b>				
Noise Figure ( $V_{DS} = 15 \text{ Vdc}$ , $V_{GS} = 0$ , $R_S = 1.0 \text{ megohm}$ , $f = 10 \text{ Hz}$ , Noise Bandwidth = 5.0 Hz)	NF	—	5.0	dB
Equivalent Input Noise Voltage ( $V_{DS} = 15 \text{ Vdc}$ , $V_{GS} = 0$ , $f = 10 \text{ Hz}$ , Noise Bandwidth = 5.0 Hz)	$e_n$	—	200	$\text{nv}/\text{Hz}^{1/2}$

(1) Pulse Test: Pulse Width  $\leq 100 \text{ ms}$ , Duty Cycle  $\leq 10\%$ .